ABSTRACT

PLASMA PROCESSING METHOD AND PLASMA PROCESSING APPARATUS

A plasma processing method according to an exemplary embodiment includes applying a first direct-current voltage to a lower electrode of a substrate support provided in a chamber of a plasma processing apparatus, in a first period during generation of plasma in the chamber. The plasma processing method further includes applying a second direct-current voltage to the lower electrode in a second period different from the first period during generation of plasma in the chamber. The second direct-current voltage has a level different from a level of the first direct-current voltage. The second direct-current voltage has a same polarity as a polarity of the first direct-current voltage.

(Fig.2)